



Irradiation of SiPM Arrays in Mu3e



Yannick Demets
for the Mu3e SciFi team:
A.Bravar, C. Grab, L. Gerritzen, C.
Martin Perez, A. Buonauro, A. Papa,
(S. Corrodi)



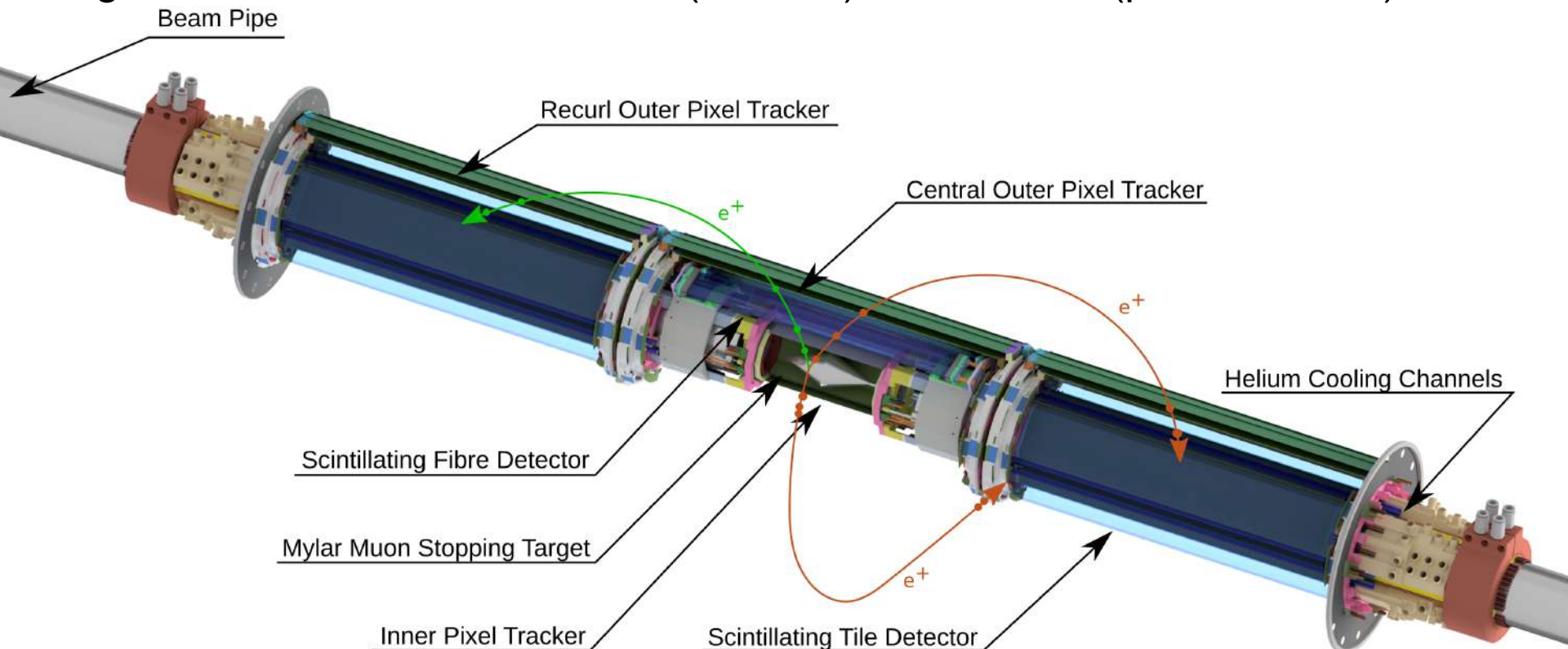
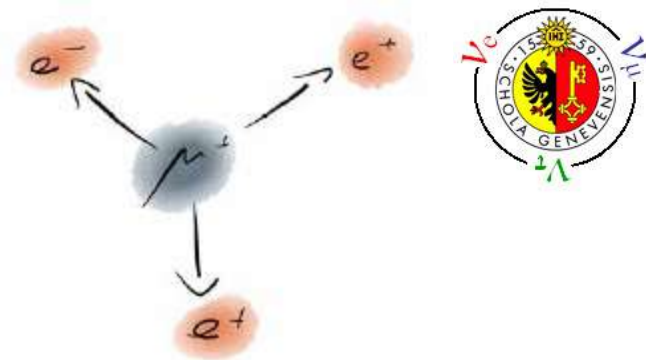
The Mu3e Experiment

Mu3e: search for the rare μ decay $\mu^+ \rightarrow e^+ e^- e^+$

with sensitivity $BR \sim 10^{-15}$ to 10^{-16} (PeV scale)

$$\tau_{(\mu \rightarrow eee)} > 1000 \text{ years } (\tau_{\mu} = 2.2 \mu\text{s})$$

using the world's most intense DC (surface) muon beam ($p \sim 28 \text{ MeV}/c$) at PSI



build a detector capable of measuring
up to 2×10^9 μ decays / s

The SciFi Detector



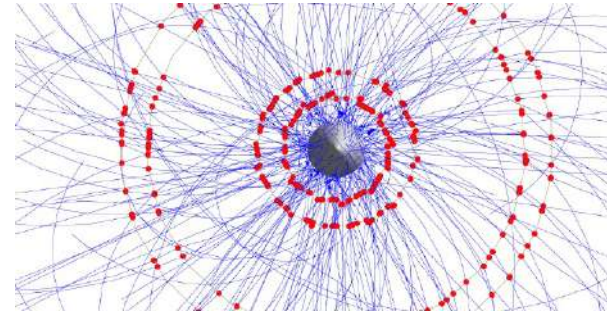
12 SciFi ribbons of 250 μm \varnothing fibers
3 staggered layers

To suppress accidental backgrounds
requires “excellent” timing :

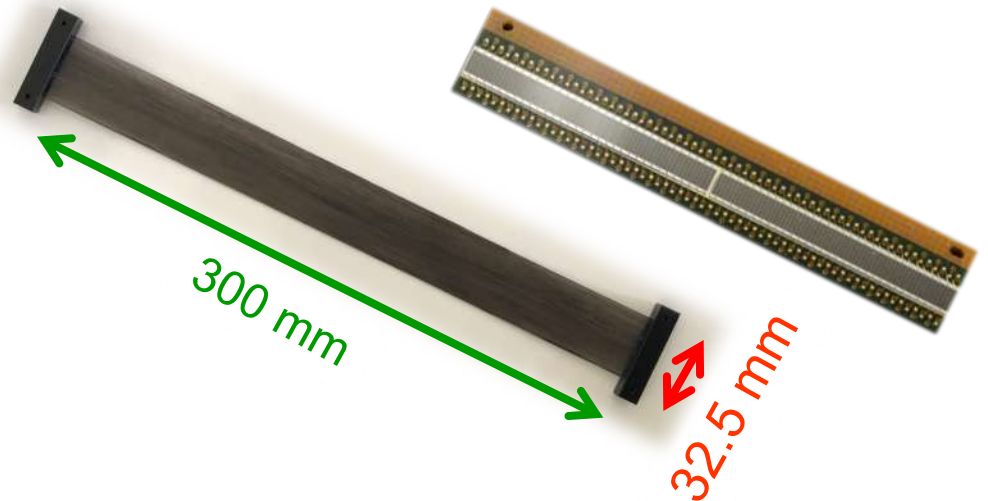
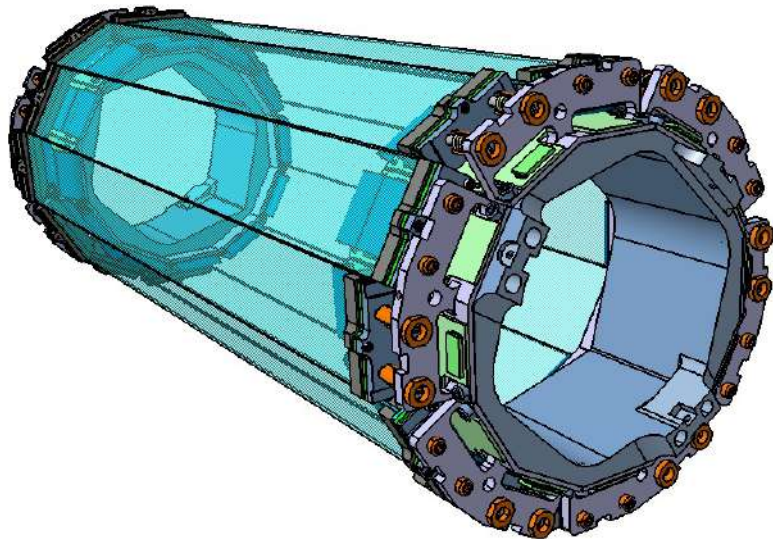
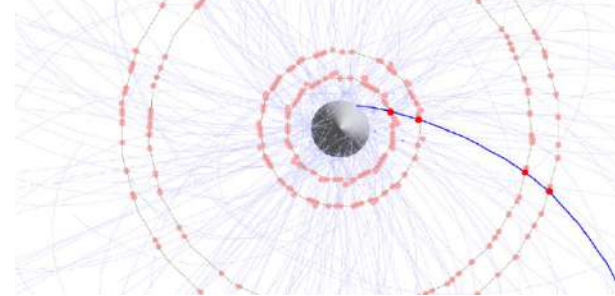
- Timing < 300 ps
- Detection efficiency > 95%

Read out with multichannel SiPM arrays

50 ns readout frame



additional ToF information < 300 ps



The SiPM Arrays

128 channel SiPM array from Hamamatsu (LHCb type) S13552HRQ

250 μm pitch

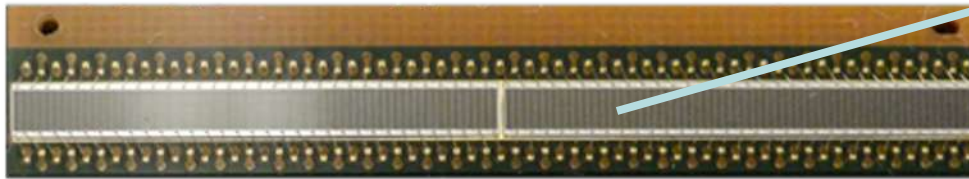
pixel size 57.5 μm x 62.5 μm

4 x 26 pixels per column

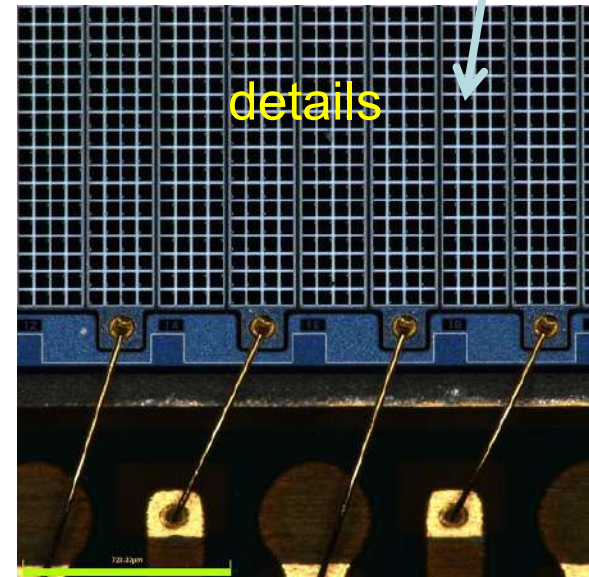
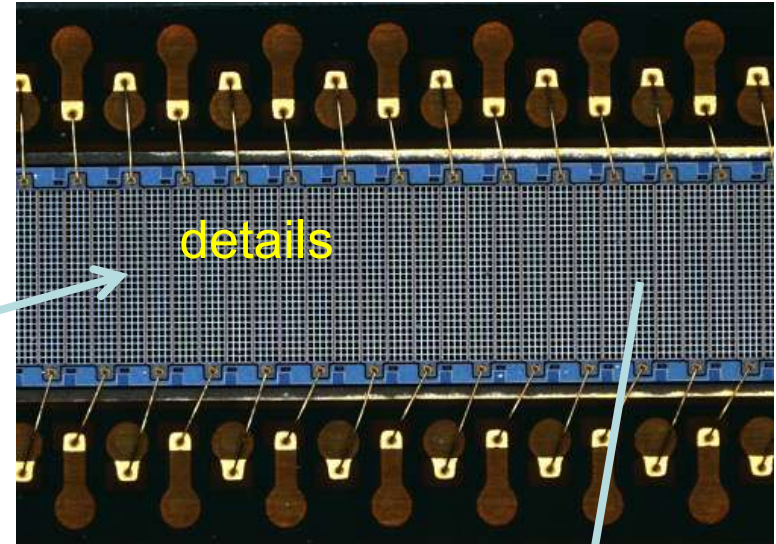
230 μm x 1625 μm column area

$V_{break} \sim 52.5 \text{ V}$ ($\pm 0.3 \text{ V}$ same array)

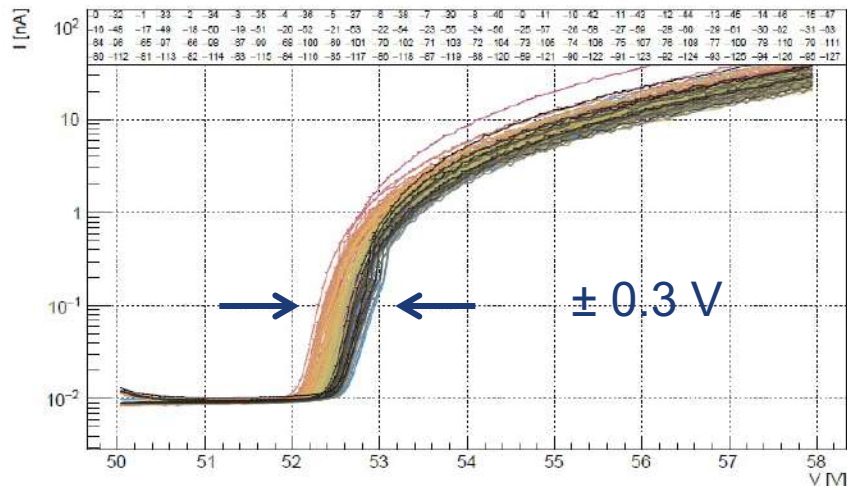
high quenching resistor



32.5 mm (two 64 ch. dyes)



IV Curves: 04_S13552_49-60V

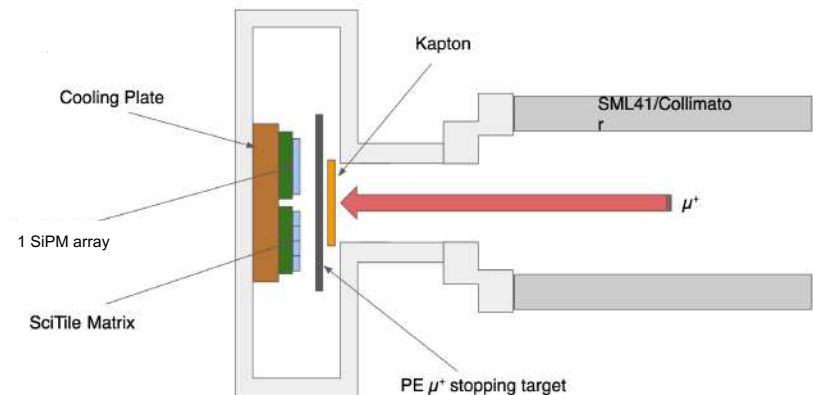
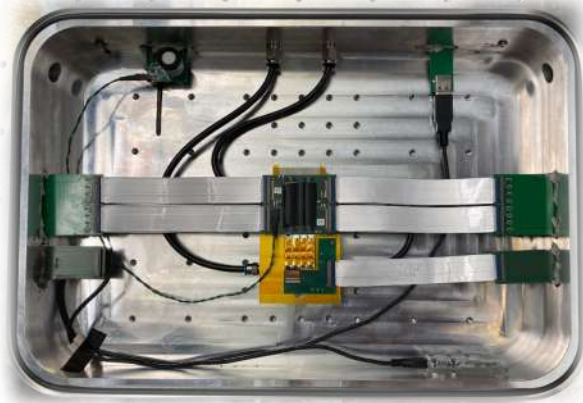
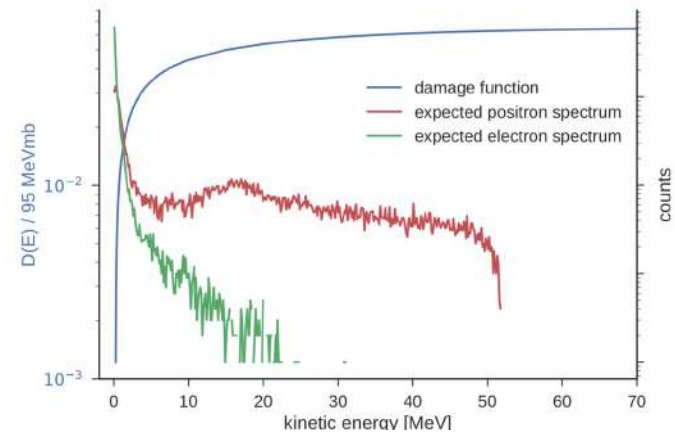


Irradiated SiPM Arrays



The radiation damage in Mu3e comes mainly from irradiation with low energy positrons up to 53 MeV

Therefore, we irradiated several SiPM arrays at different doses in PiE5 using positrons from muon decays at rest (i.e. Michel electrons)



In phase I (i.e. 2.5×10^{15} muons stops) the SiPM arrays will absorb a dose of $O(10^{11})$ neutrons equivalent / cm^2 .

In this study: 5 irradiated SiPMs at different doses.

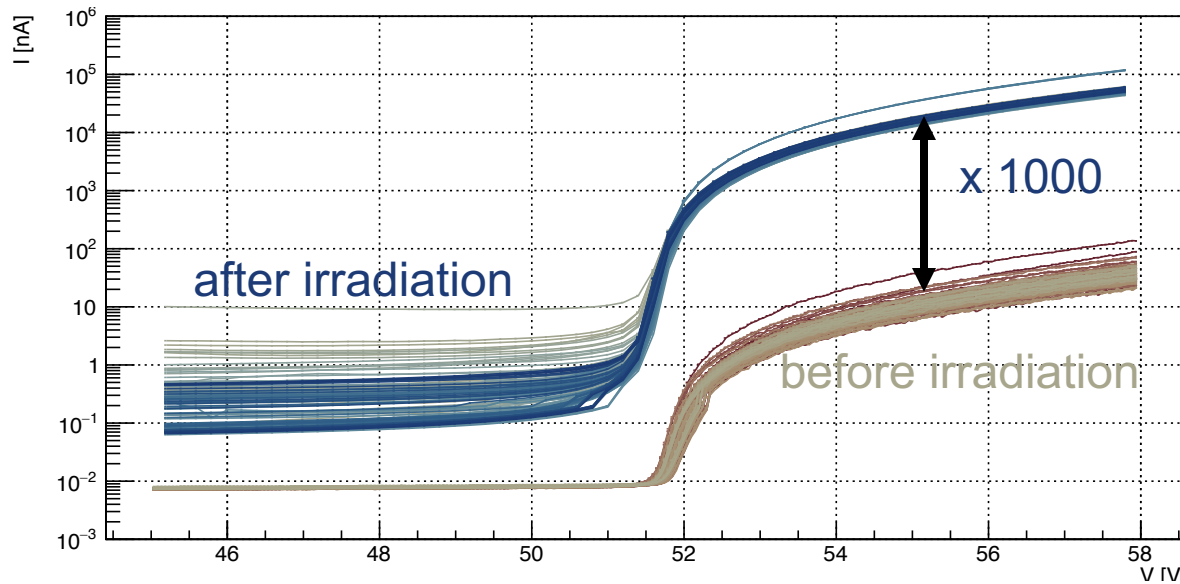
The maximum dose corresponds to $\sim 10^{12}$ part./ cm^2 .

(conversion between positrons and $\text{neutron}_{\text{eq}}$ is not straightforward)

I-V Curves



I-V curve



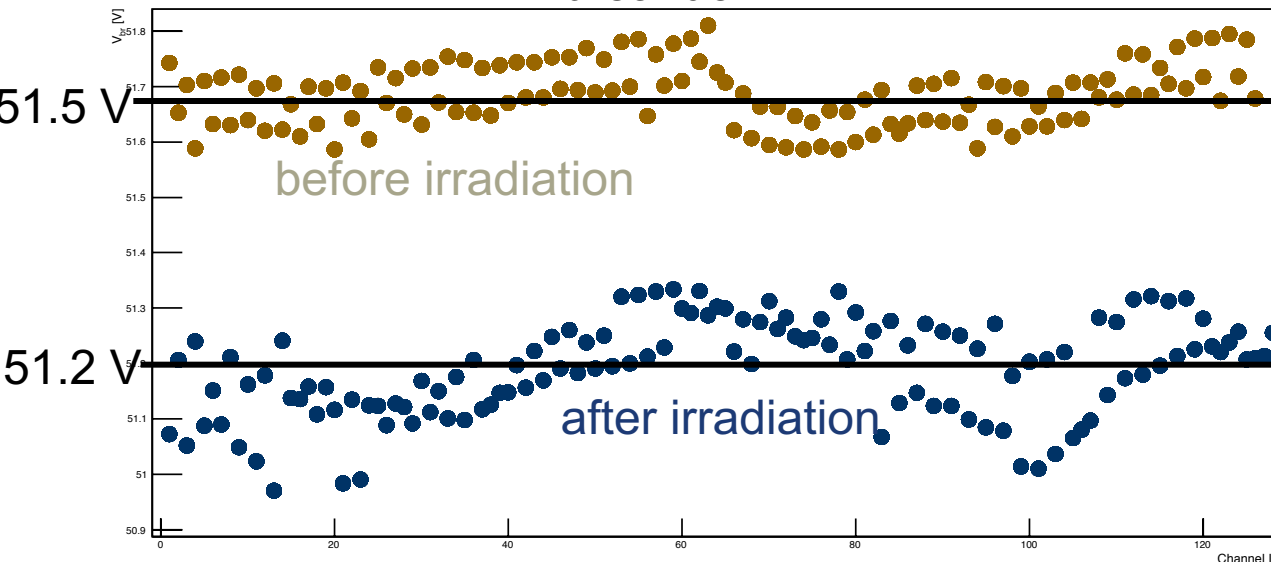
at room temperature $\sim 25^\circ \text{C}$

after irradiation,
before annealing

Maximum dose SiPM

Note: area = 26 mm^2 ,
i.e. $\frac{1}{4} \text{ cm}^2$

breakdown V

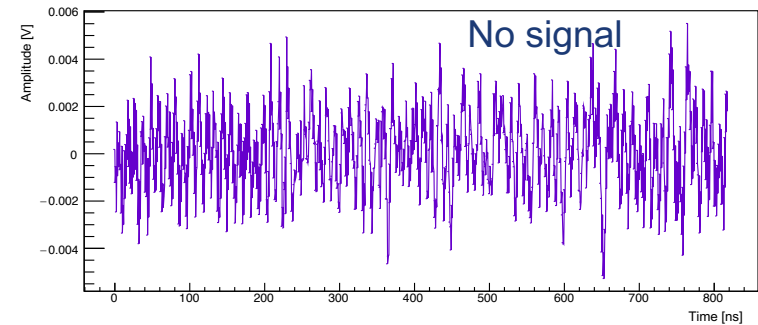
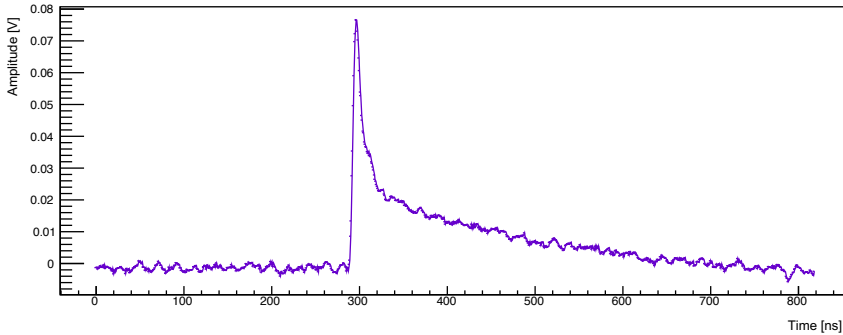


Waveforms

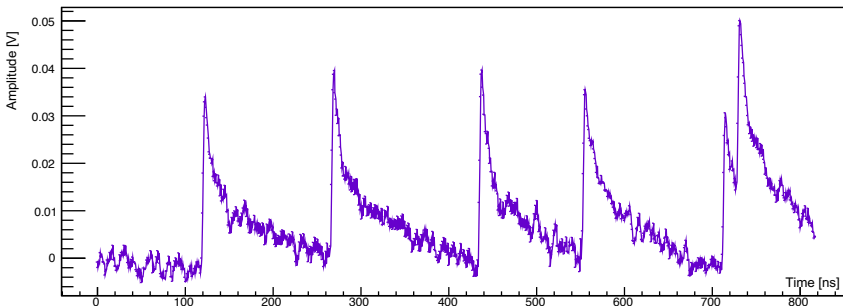
Waveforms after amplification with gain 40 dB,
using a random trigger and with a bias voltage $V_{bd} + 3V$
Maximum dose SiPM

irradiated at -7°C

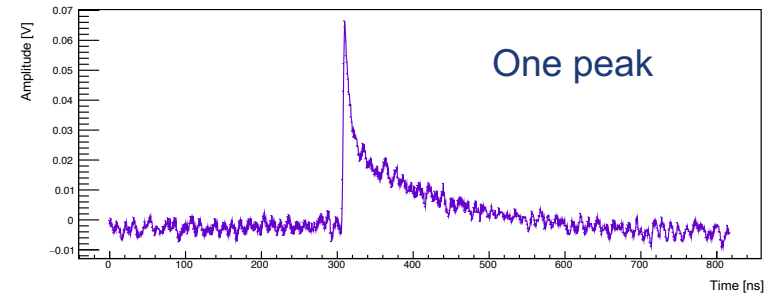
Not irradiated



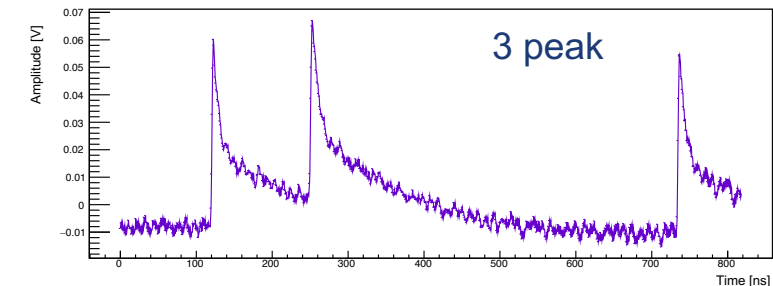
irradiated at 20°C



One peak



3 peak

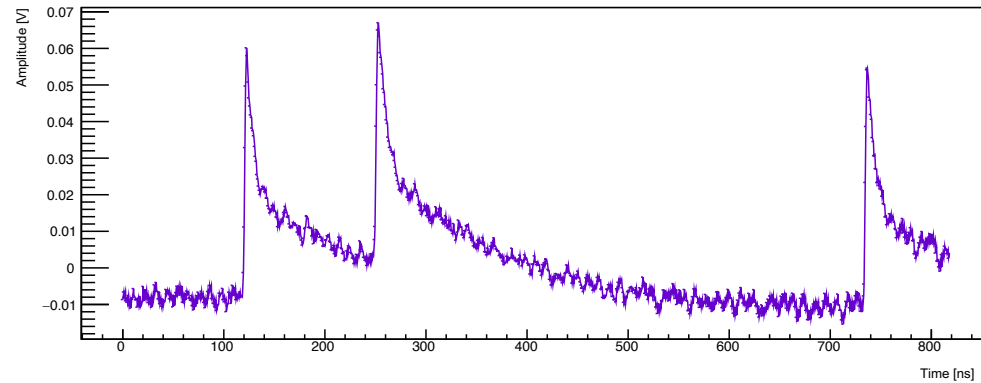


“Dark Count Rates”



To estimate the dark count rate we count the number of “peaks”
in the waveforms recorded with the DRS4 waveform digitizer over a 800 ns “gate” (normalize to 1 s)

Counting peaks by “eye”
bias voltage $V_{bd} + 3V$



irradiation dose full dose

Irradiated at 20°C : ~2.5 MHz/channel

Irradiated at 10°C : ~1.6MHz/channel

Irradiated at 0°C : ~0.7 MHz/channel

Irradiated at -7°C : ~0.4 MHz/channel

Prospect :

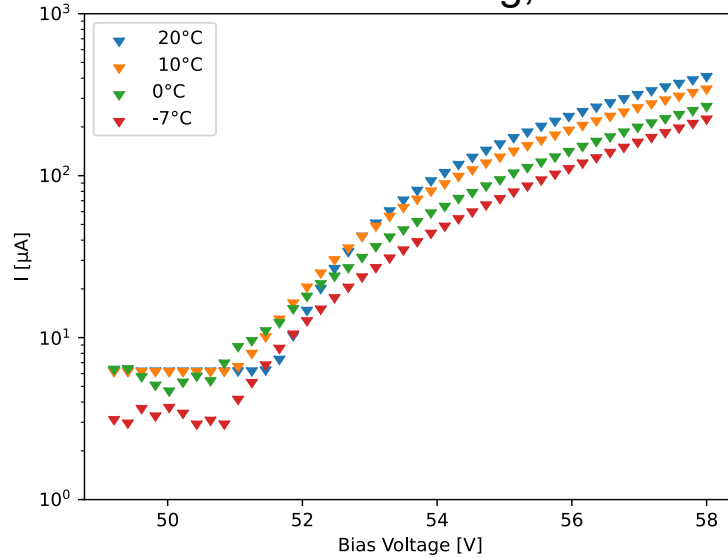
At -20°C expect ~ 100 kHz/channel

Dark Current vs V_{bias} for Different T

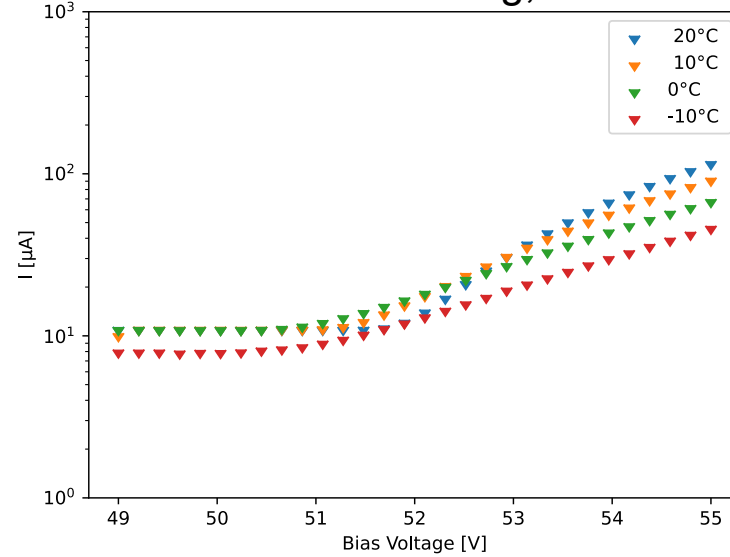


After annealing months at room temperature

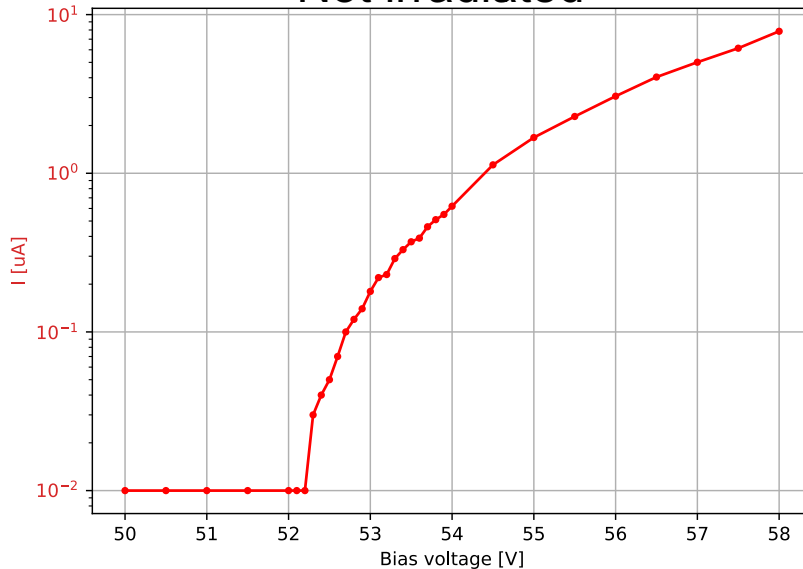
Irradiated after annealing, max dose



Irradiated after annealing, $\sim 1/2$ of max dose

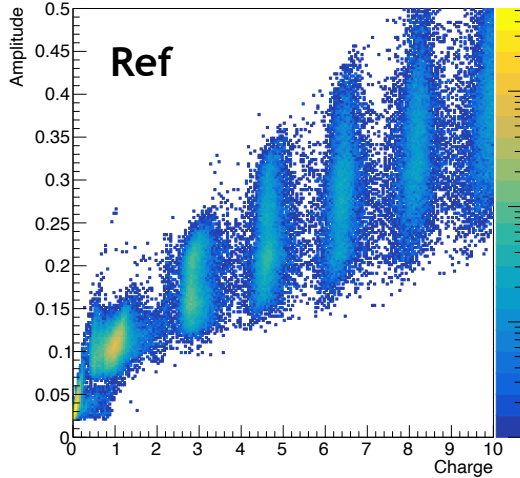


Not irradiated

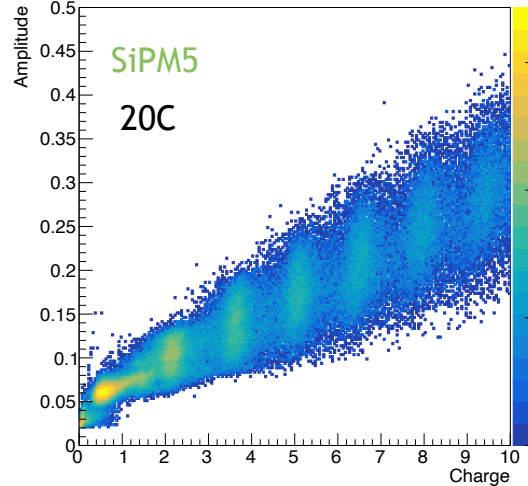


Amplitude vs. Charge

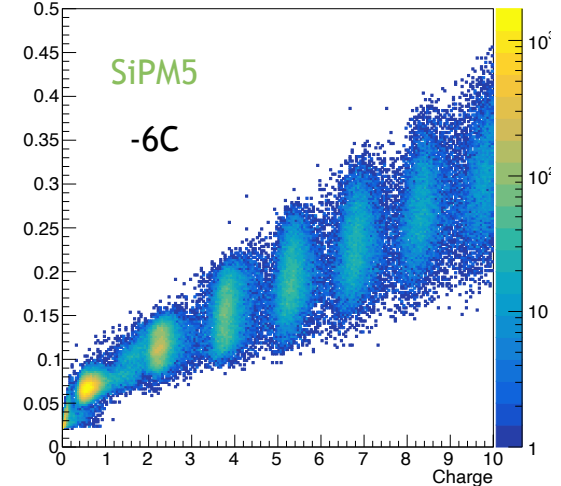
non-irradiated



irradiated at 20⁰ C



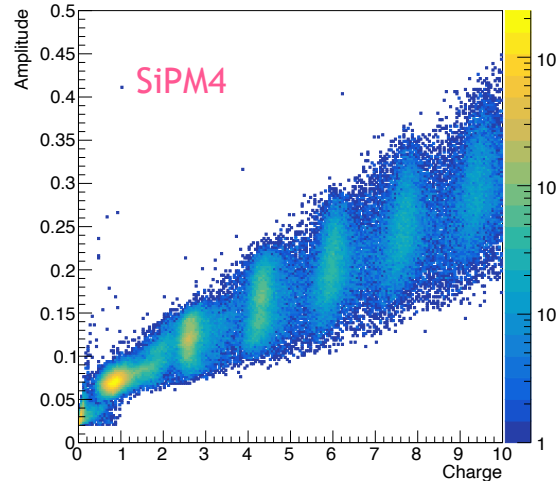
irradiated at -6⁰ C



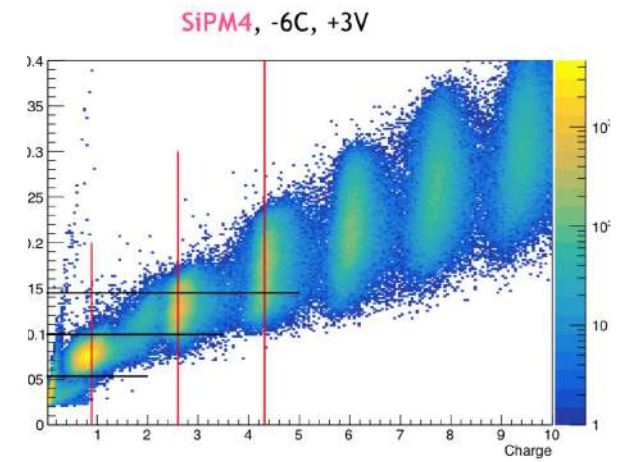
At bias voltage $V_{bd} + 3V$

SiPM 5: $\sim \frac{1}{2}$ max dose
 SiPM 4 $\sim \frac{1}{4}$ max dose
 (irradiation max dose
 i.e. $\sim 10^{11}$ n_{eq}/cm²)

irradiated at 20⁰ C



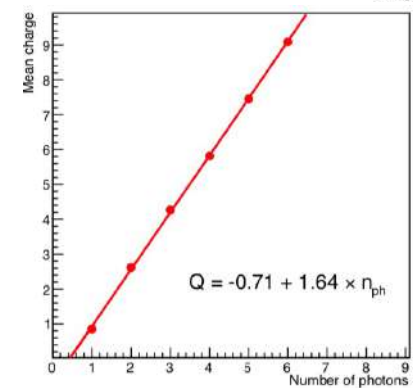
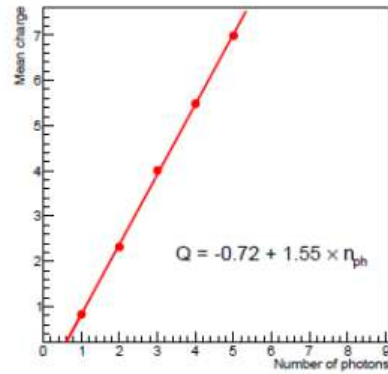
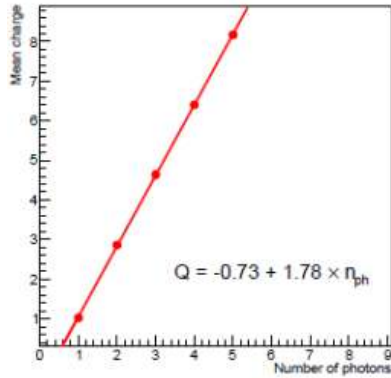
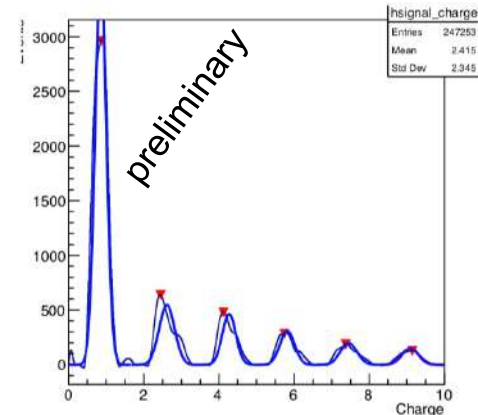
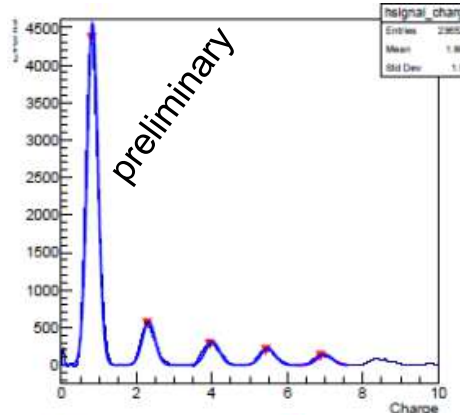
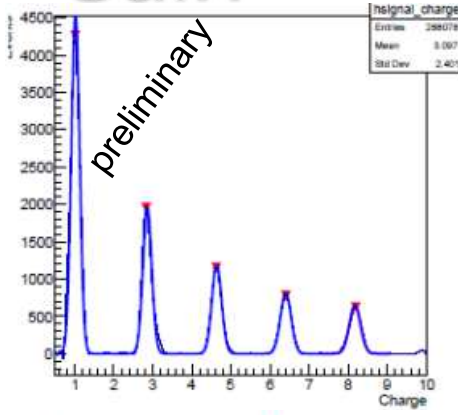
irradiated at -6⁰ C



As the temperature drops, we recover single-photon resolution,
 allowing for a correct threshold determination (no clustering in these plots)

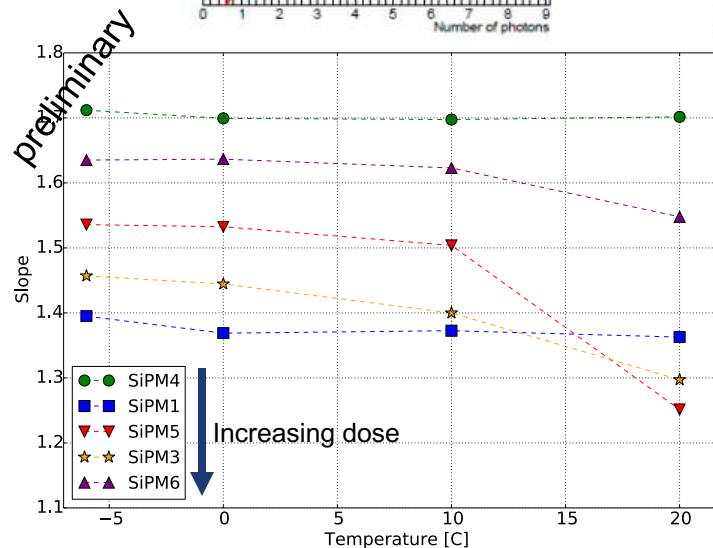
Gain

charge
linearity (baseline subtracted)



At bias voltage $V_{bd} + 3V$

SiPM6 max dose
(irradiation full dose
(i.e. $\sim 10^{11} n_{eq}/cm^2$)
SiPM 5: $\frac{1}{2}$ max dose
SiPM 4 $\frac{1}{4}$ max dose



Slope = relative gain

Left-Right Correlations

Only one side irradiated SiPM

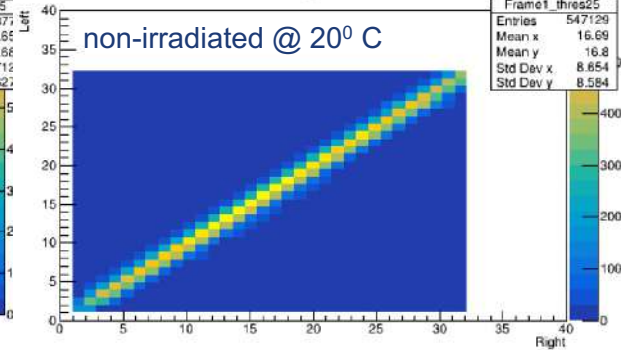
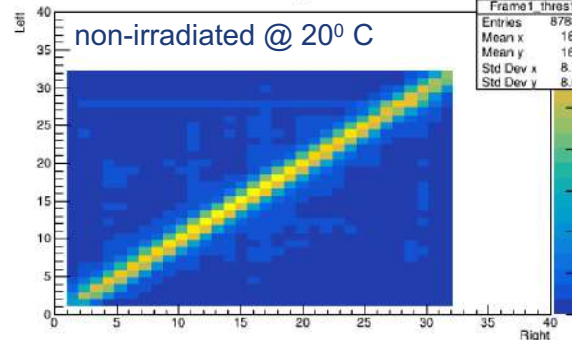
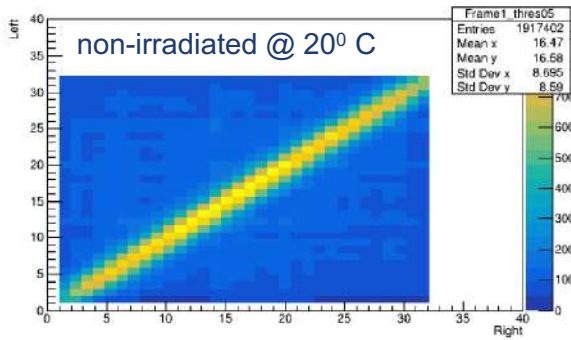


threshold 0.5 ph.e.l.

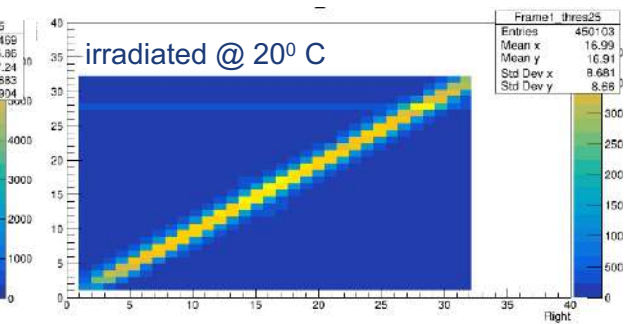
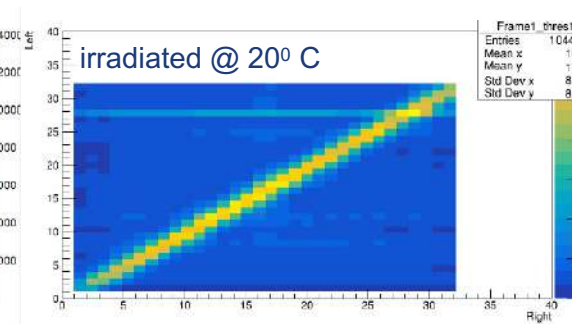
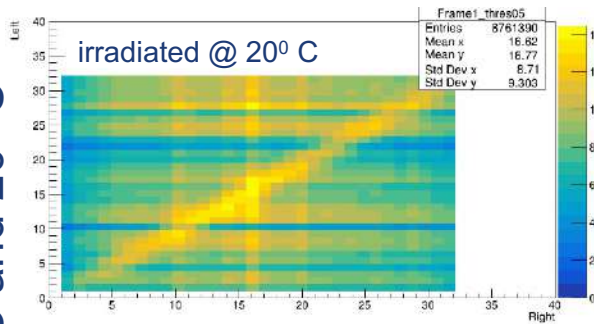
threshold 1.5 ph.e.l.

threshold 2.5 ph.e.l.

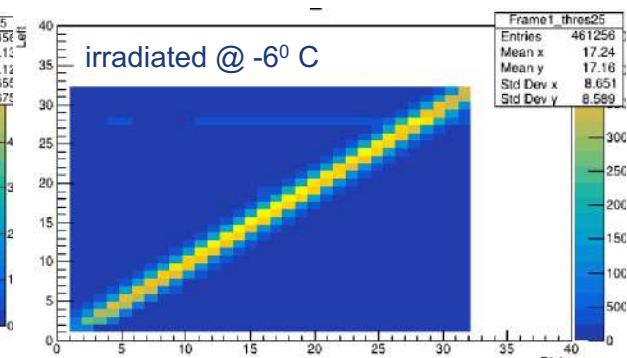
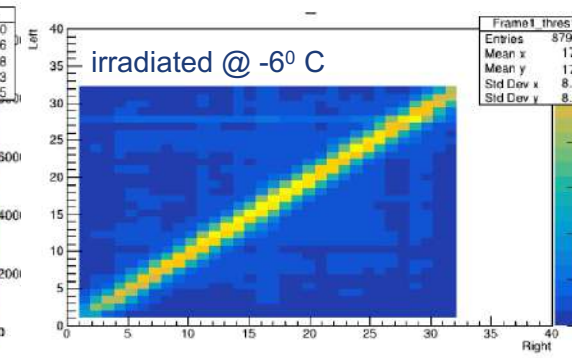
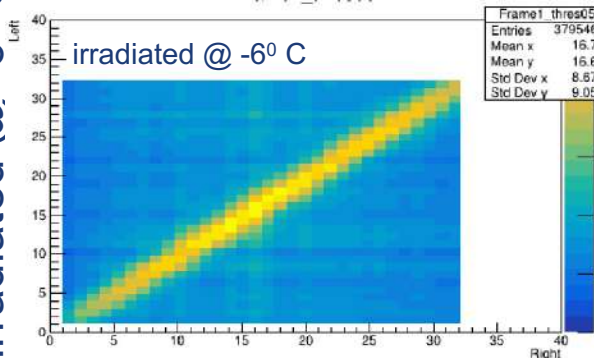
non-irradiated @ 20° C



irradiated @ 20° C and 20° C



irradiated @ -6° C



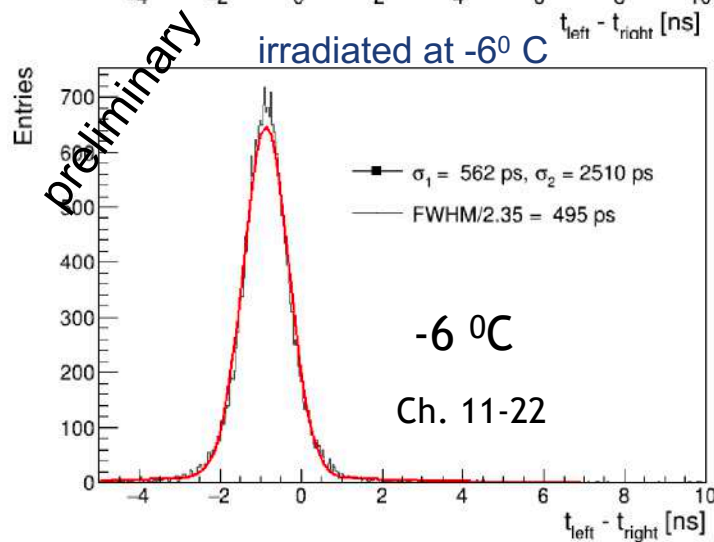
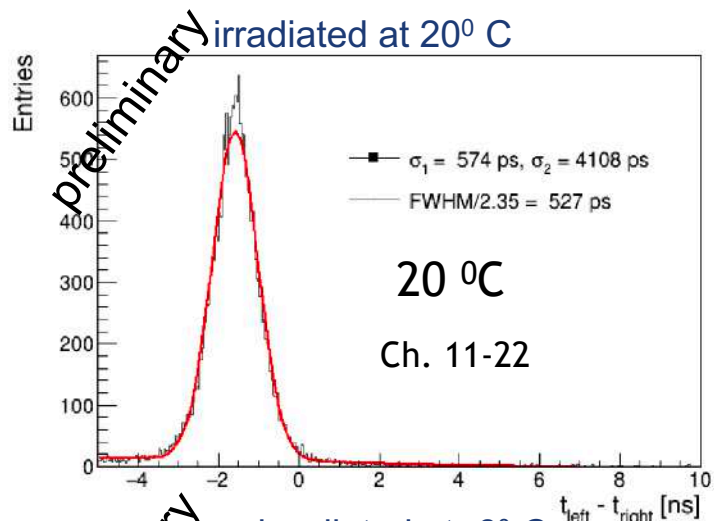
from the correlation plot one can “guess” the cluster size.

With SiPM6 max dose

Timing performance

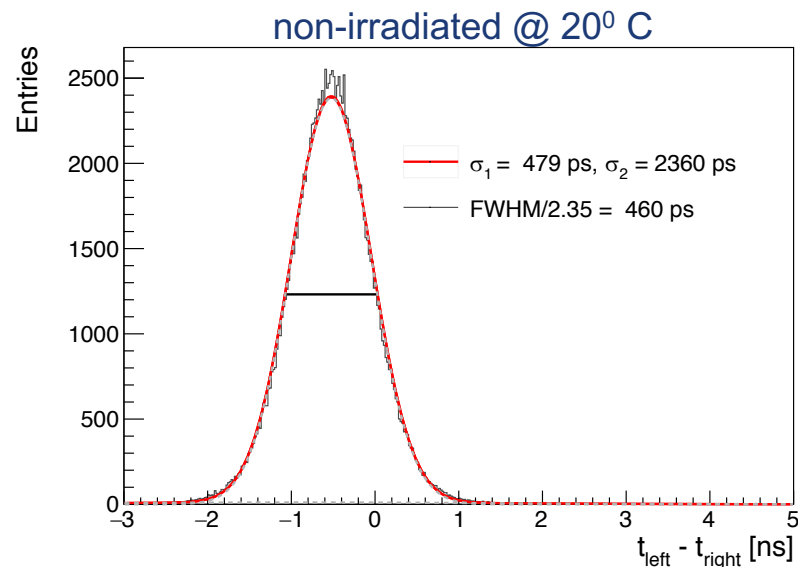


Only one side irradiated SiPM



Affects the time resolution compared to the time resolution of the non irradiated SiPM (only one side)

Improves with cooling



With SiPM5 $\sim \frac{1}{2}$ max dose

Noise Reduction



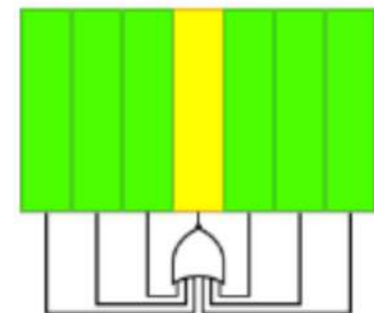
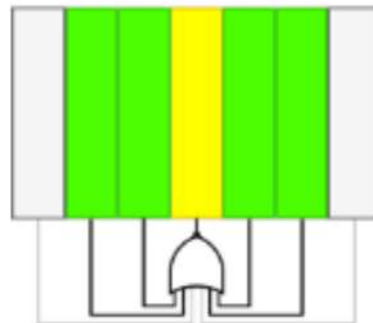
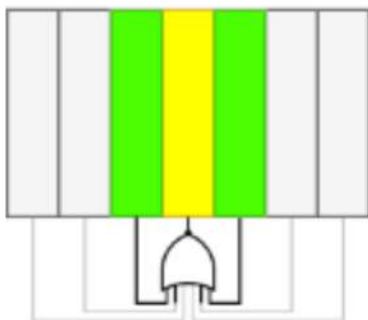
➤ Clustering

goal of the clustering algorithm is to group signals caused by an ionizing particle together while **eliminating any unwanted contribution from accidentally fired SiPM channels**

➤ Time matched clusters

allows for more constraining and therefore better identification when a particle crosses one SciFi ribbon

- ## ➤ MuTRiG2 clustering algorithm embedded in ASIC (Coincidence logic)
- Hits are only **stored if a coincidence with a neighboring channel is seen**. Neighbors can be selected from a matrix of **3 nearest neighbors**, for each channel independently.



Conclusions



- ❖ Work in progress. Studies on irradiated SiPM's are ongoing.
- ❖ At beamtest studies has been done and analysis is ongoing.
- ❖ Lab studies are in progress

- ❖ If necessary, replace SIPM arrays (already foreseen)
- ❖ Higher threshold : if thresholds at 1.5 ph.e. , depending on how we implement the algorithm, no efficiency loss.
- ❖ Cooling

- ❖ Ignorant question :
Is it possible to conceive a SiPM resistant to electron radiation ?

Thank you.